Topological Insulators in Three D im ensions

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W e study three dimensional generalizations of the quantum spin H all (Q SH) e ect. Unlike two dimensions, where the Q SH e ect is distinguished by a single Z₂ topological invariant, in three dimensions there are 4 invariants distinguishing 16 \topological insulator" phases. There are two general classes: weak (W T I) and strong (ST I) topological insulators. The W T I states are equivalent to layered 2D Q SH states, but are fragile because disorder continuously connects them to band insulators. The ST I states are robust and have surface states that realize the 2+1 dimensional parity anomaly without ferm ion doubling, giving rise to a novel \topological m etal" surface phase. W e introduce a tight binding m odel which realizes both the W T I and ST I phases, and we discuss the relevance of this m odel to real three dimensional m aterials, including bism uth.

PACS num bers: 73.43.-f, 72.25.Hg, 73.20.-r, 85.75.-d

In recent years, the advent of spintronics has motivated the study of the e ects of spin orbit interactions (SO I) on the electronic structure of solids. SO I leads to the spin Halle ect[1, 2], which has been observed in G aA s[3, 4]. We proposed [5] that in graphene the SO I leads to the quantum spin Hall (Q SH) e ect. In the Q SH phase there is a bulk excitation gap along with gapless spin-

Itered edge states. The Q SH phase is distinguished from a band insulator by a Z_2 topological invariant [6], which is a generalization applicable to time reversal invariant systems of the TKKN invariant of the integer quantum H all e ect[7]. Because of the weak SO I in carbon, the SO I induced energy gap in graphene is likely to be quite sm all[8]. How ever, M urakam ihas recently suggested that bism uth bilayers may provide an alternative venue for the Q SH e ect[9]. This breakthrough provides a new direction for the experim ental observation of this phase.

In this paper we consider the generalization of the Q SH e ect to three dimensions (3D). Our work builds on recent progress by M oore and B alents [10], who show ed that time reversal invariant energy bands in 3D are characterized by four Z₂ invariants, leading to 16 classes of \topological insulators". A sim ilar result has also been obtained by Roy [11]. Here, we will explain the physical m eaning of these invariants and characterize the phases they distinguish. One of the four invariants is of special signi cance and distinguishes what we will refer to as \weak" and \strong" topological insulators. W ith disorder, the weak topological insulator (W T I) is equivalent to a band insulator, while the strong topological insulator (ST I) rem ains robust. W e show W T Is and ST Is have surface states with an even and odd number of Dirac points respectively. The latter case leads to a new \topological metal" surface phase, which we characterize. We introduce a tight binding model on a distorted diam ond lattice, which realizes both the W TI and STI phases, allowing the surface states to be studied explicitly.

In Ref. 12 we established the connection between the Z_2 invariant for the bulk Q SH phase and the spin ltered edge states. We begin by reviewing that argument in a

way which makes the generalization to 3D transparent. The 2D invariant can be understood using a Laughlin type construction [13] on a cylinder threaded by m agnetic ux = 0 or (in units of h=e). The invariant characterizes the change in the time reversal polarization (TRP), which signals the presence of a K ram ers degeneracy at the ends, when is changed from 0 to . If the cylinder consists of a single unit cell in the circum ferential (x) direction, then the magnetic ux threading the cylinder plays the role of the crystalm om entum k_x in band theory. The spectrum of the discrete end states of the cylinder as a function of ux then re ects the edge state spectrum as a function of m om entum. The change in the TRP as a function of ux determines the way the K ram ers degenerate end states at the edge time reversal invariant m om enta (TRIM) k_x = $_1$ = 0 and k_x = $_2$ = are connected to each other. In the Q SH phase the K ram ers pairs \switch partners" (Fig. 1a), re ecting the change in the TRP, while in the conventional insulator (Fig. 1b) they do not. It follows that in the QSH phase edge states traverse the bulk energy gap, and cross the Ferm i energy an odd num ber of tim es between a and b. In the insulating phase, the edge states cross the Ferm i energy an even num ber of tim es if at all. They are not topologically protected, since changes in the Ham iltonian at the edge can push the entire edge band out of the bulk gap.

The change in the TRP between $_1$ and $_2$ is related to the bulk band structure, de ned for a 2D system with periodic boundary conditions in both directions. The 2D B rillouin zone has four TRIM, $_1$, which are related to

 $_{i}$ by a reciprocal lattice vector. For an edge perpendicular to G the 1D edge TR IM $_{a=1;2}$ are projections of pairs $_{i=a1}$, $_{i=a2}$, which satisfy $_{a1}$ $_{a2}$ = G =2, onto the line perpendicular to G.

The TRP associated with a can be expressed as $a = a_{1} = a_{2}$, where [12]

$$_{i} = {}^{p} \overline{\text{Det}[w(i)]} = P f[w(i)] = 1:$$
 (1)

Here the unitary matrix $w_{ij}(k) = hu_i(k)j ju_j(k)i$. At $k = i, w_{ij} = w_{ji}$, so the P fa an P f[w] is de ned. a is

FIG.1: Schem atic surface (or edge) state spectra as a function of momentum along a line connecting $_{a}$ to $_{b}$ for (a) $_{a}$ $_{b}$ = 1 and (b) $_{a}$ $_{b}$ = +1. The shaded region shows the bulk states. In (a) the TRP changes between $_{a}$ and $_{b}$, while in (b) it does not.

free of the am biguity of the square root in (1), provided the square root is chosen continuously as a function of k. However, a is not gauge invariant. A k dependent gauge transform ation can change the sign of any pair of i's. This re ects the physical fact that the end K ram ers degeneracy depends on how the crystal is term inated. It is sim ilar to the am biguity of the charge polarization [12]. The product, 1 = 2 = 1 = 2 = 3 = 4, is gauge invariant, and characterizes the change in TRP due to changing the ux from 1 = 0 to 2 = 0. This de nes the single Z₂ invariant in 2D, and using the above argum ent, determ ines the connectivity of the edge state spectrum.

In 3D there are 8 distinct TRM, which are expressed in terms of primitive reciprocal lattice vectors as $_{i=(n_1n_2n_3)} = (n_1b_1 + n_2b_2 + n_3b_3)=2$, with $n_j = 0$; 1. They can be visualized as the vertices of a cube as in Fig. 2. A gauge transform ation can change the signs of $_i$ associated with any four $_i$ that lie in the same plane. M odulo these gauge transform ations, there are 16 invariant con gurations of $_i$. These can be distinguished by 4 Z₂ indices $_0$; ($_{1 \ 2 \ 3}$), which we de ne as

(1)
$$^{\circ} = \prod_{\substack{n_1 n_2 n_3 \\ n_j = 0; 1 \\ Y}}^{I}$$
 (2)

1)
$$_{i=1;2;3}^{i=1;2;3} = _{n_1n_2n_3}$$
: (3)
 $n_{j6 i} = 0;1; m_i = 1$

 $_{0}$ is independent of the choice of b_{k} . (p_{2} $_{3}$) are not, but they can be identified with G $_{i}$ $_{i}b_{i}$, which belongs to the 8 element mod 2 reciprocal lattice, in which vectors that dier by 2G are identified. ($_{1}$ $_{2}$ $_{3}$) can be interpreted as M iller indices for G .

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⁰ 4 are equivalent to the four invariants introduced by M oore and Balents using general hom otopy arguments. The power of the present approach is that it allows us to characterize the surface states on an arbitrary crystal face. Generalizing the Laughlin argument to 3D, consider a system with open ends in one direction and periodic boundary conditions in the other two directions. This can be visualized as a torus with a nite thickness (a \C orbino donut"), which has an inside and an outside surface. Viewed as a 1D system, we then seek to clas-

FIG.2: D lagram s depicting four di erent phases indexed by $_{0}$; $(1 \ 2 \ 3)$. (a) depicts $_{i}$ at the TRIM $_{i}$ at the vertices of the cube. (b) characterizes the 001 surface in each phase. The surface TRIM $_{a}$ are denoted by open (lled) circles for $_{a} = _{a1} _{a2} = +1(1)$. They are projections of $_{a1}$ and $_{a2}$, which are connected by solid lines in (a). The thick lines and shaded regions in (b) indicate possible surface Ferm i arcs which enclose speci c $_{a}$.

sify the changes in the K ram ers degeneracy associated with the surfaces as a function of two uxes threading the torus (or equivalently as a function of the two com ponents of the surface crystalm om entum).

For a surface perpendicular to G, the surface B rillouin zone has four TR M $_{a}$ which are the projections of pairs $_{a1}$, $_{a2}$, that di er by G =2, into the plane perpendicular to G. D ue to K ram ers' degeneracy, the surface spectrum has two dimensionalD irac points at $_{a}$. The relative values of $_{a} = _{a1 \ a2}$ determ ine how these D irac points are connected to one another, as illustrated in Fig. 1. For any path connecting $_{a}$ to $_{b}$, the surface band structure will resemble Fig. 1a (lb) for $_{a \ b} = 1$ (+ 1), and the surface bands will intersect the Ferm intergy an odd (even) number of times. It follows that the surface Ferm i arc divides the surface B rillouin zone into two regions. The D irac points at the TR M $_{a}$ with $_{a} = +1$ are on one side, while those with $_{a} = 1$ are on the other side.

In Fig. 2 we depict $_{\rm i}$ for four di erent topological classes, along with the predictions for the edge state spectrum for a 001 face. The surface Ferm i arc encloses either 0(4), 1(3), or 2 D irac points. When the number of D irac points is not 0(4), there must be surface states which connect the bulk conduction and valence bands.

There are two classes of phases depending on the parity of $_0$. For $_0 = 0$ each face has either 0(4) or 2 enclosed D irac points. For a face G = $_{i}m_{i}b_{i}$ there are 0(4) D irac points for $m_{i} = _{i}m \text{ od } 2$ (i = 1;2;3) and 2 D irac points otherwise. These phases can be interpreted as layers of 2D Q SH states stacked in the G direction. They resemble three dimensional quantum H all phases[14], which are indexed by a triad of C hern integers that de ne a reciprocal lattice vector G perpendicular to the layers and give the conductivity $_{ij} = (e^2 = h)"_{ijk}G_k = (2)$. In the present case, G is dened m odulo 2G, so that layered Q SH phases stacked along G and G + 2G are equivalent.

FIG.3: Energy bands for (a) them odel (4) with t = 1, so = :125. The symmetry points are = (0;0;0), X = (1;0;0), W = (1;1=2;0), K = (3=4;3=4;0) and L = (1=2;1=2;1=2) in units of 2 = a. The dashed line shows the energy gap due to $t_1 = :4$. (b) shows the phase diagram as a function of t_1 and t_2 (for bonds in the 111 and 111 directions) with phases indexed according to cubic M iller indices for G . The shaded region is the ST I phase.

The presence or absence of surface states in the $_0 = 0$ phases is delicate. For the 0;(001) phase in Fig. 2, the 100 face has two D irac points, while the 801 face has 0(4). This sensitivity is a symptom of the fact that the topological distinction of these phases relies on the translational symmetry of the lattice. Indeed, if the unit cell is doubled, the two D irac points fold back on one another. A weak periodic potential then opens a gap. It is thus likely that disorder will elim inate the topological distinction between these phases and simple insulators. Surface states will generically be localized. For this reason, we refer to the $_0 = 0$ phases as \weak" topological insulators. N onetheless, the weak invariants have in portant im plications for clean surfaces.

The $_0 = 1$ phases are more robust, and we refer to them as \strong" topological insulators. In this case the surface Ferm i arc encloses 1 (3) D irac points on all faces. If the Ferm i energy is exactly at the D irac point this provides a time reversal invariant realization of the 2+1 dim ensional parity anom aly [15, 16, 17, 18] without ferm ion doubling. This can occur because the D irac point partners reside on opposite surfaces. For a generic Ferm i energy inside the bulk gap the surface Ferm i arc will enclose a single Dirac point. This de nes a two dimensional \topologicalm etal" that is topologically protected because a quantized Berry's phase of is acquired by an electron circling the Ferm i arc. This Berry's phase im plies that with disorder the surface is in the symplectic universality class [19, 20], which is not localized by weak disorder.

To develop an explicit m odel of these phases we consider a 4 band tight binding m odel of s states on a diam ond lattice with SO I, that generalizes the 2D honeycom b lattice m odel[5, 16, 18].

$$H = t \sum_{\substack{hiji \\ hiji}}^{X} c_{j}^{v} c_{j} + i(8 _{SO} = a^{2}) \sum_{\substack{hhijii \\ hhijii}}^{X} c_{j}^{v} s \quad (a_{j}^{b} - a_{j}^{2}) c_{j}: (4)$$

The rst term is a nearest neighbor hopping term connecting the two fcc sublattices of the diam ond lattice. The second term connects second neighbors with a spin dependent am plitude. $d_{ij}^{1/2}$ are the two nearest neighbor bond vectors traversed between sites i and j. a is the cubic cell size. The energy bands are shown in Fig. 3a. D ue to inversion symmetry, each band is doubly degenerate. The conduction and valence bandsmeet at 3D D irac points at the three inequivalent X points X^r = 2 f=a, where r = x;y;z. This degeneracy is lifted by symmetry low ering m odulations of the four nearest neighbor bonds t! t+ t_p , with p = 1; ...; 4.

Near X z the low energy e ective m ass m odel has the form of a 3+1 dimensionalD irac equation,

$$H_{e}^{z} = ta^{y}q_{z} + 4_{so}a^{z}(s^{x}q_{x} - s^{y}q_{y}) + m^{z}$$
 (5)

Here q = k X^z and m^z = P_{p} t_psgn[d_p 2]. d is the bond vector associated with the p'th nearest neighbor bond. The Pauli matrices ⁱ are associated with the sublattice degree of freedom, while sⁱ describe the spin. H^{x;y}_e are the sam e with x, y and z permuted in d and sⁱ, but not ⁱ. Transitions between di erent phases occur when the masses at any of the X^r vanish. t_p = 0 is thus a multicritical point separating 8 di erent tim e reversal invariant phases.

Determ ining $_{i}$ for these phases using (1-3) requires eigenvectors that are de ned continuously throughout the Brillouin zone[12]. Since the Chem integers vanish, this is always possible. Determ ining the appropriate phases numerically, however, is nontrivial. An alternative (though tedious) numerical approach would be to characterize the P fa an function introduced in Ref. 6. Generalizing the results of Ref. 12 it can be shown that the product of 4 $_{i}$ in any plane is related to the zeros of the P fa an in that plane, which can be identied without choosing phases. For the present problem, however, we are fortunate because the eigenvectors can be determ ined analytically, allowing for the continuation of w_{ij}(k) between the di erent $_{i}$. We nd

$$\sum_{i=sgn[}^{X} (t + t_{p}) \cos_{i} (q d_{1})]:$$
(6)

For small t_p , = 1 at k = 0 and at 3 of the L points. = 1 at the 4th L point. At X^r, = sgn [m^r]. W hen one of the four bonds is weaker than the others ($t_p < 0$, $t_{(p^0 \in p)} = 0$ for instance) the system is in a W T I phase, which m ay be interpreted as a Q SH state layered in the d_p direction. There are 4 such states, depending on p, of which two are shown in Fig. 3b. We labeled the phases with the conventional cubic M iller indices for G . 111 and 111 are distinct elements of the foc m od 2 reciprocal lattice. W hen one of the bonds is stronger than the others the system is in one of four ST I phases. The band insulator 0; (000) is not perturbatively accessible from this critical point. However, in the tight binding m odel

FIG.4:2D band structures for a slab with a 111 face for the four phases in Fig. 3. The states crossing the bulk energy gap are localized at the surface. In the W TI (STI) phases there are an even (odd) number of D irac points in the surface spectrum. The inset shows the surface B rillouin zone.

it occurs when one bond is turned up so that $t_i > 2t$. A staggered sublattice potential also leads to a band insulator, but the strength must exceed a nite value (set by s_0) before that transition occurs.

To study the surface states, we solve (4) in a slab geometry. Fig. 4 shows the 2 dimensional band structures of the four phases in Fig. 3 for a slab parallel to the 111 surface along lines that visit each of the four TR IM. The plots with the same $_0$ can be viewed as di erent faces of the same state. The bulk states above the bandgap are clearly seen. In addition, there are surface states which traverse the gap. In the W T I phases 0; (111) and 0; (111) there are 0 and 2 2D D irac points, on both the top and bottom surfaces, as expected from the general arguments given above. In the ST I phases 1; (111) and 1; (111) there is 1 (3) D irac point on each surface. In each case, the non degenerate surface states near the D irac points are spin litered, such that hs (k)i = hs(k)i. Spin density and charge current are thus coupled.

Though the 4 band diam ond lattice model is simple, it is probably not directly relevant to any speci c material. However, it may give insight into the behavior of real crystals. Consider a sequence of crystal structures obtained from diam ond by continuously displacing the fcc sublattices in the (111) direction:

diam ond ! graphite (ABC) ! cubic:

Starting with diam ond, the 111 nearest neighbor bond is stretched, leading to the 0; (111) W T I phase. As the sublattice is displaced further both sublattices eventually reside in the sam e plane with a structure sim ilar to ABC stacked graphite. D isplacing further, the lattice eventually becom es cubic. At this point, the gap closes, and the system is m etallic. The s state m odel rem ains in the W T I phase up to the cubic point. B ism uth has the rhom bohedral A 7 structure, which can be viewed as a cubic lattice distorted \tow and diam ond", along with a trigonal distortion of the fcc B ravais lattice. M urakam i show ed that a bilayer of bism uth, whose structure is sim ilar to a single plane of graphene, is in the Q SH phase. This suggests that for weak coupling between bilayers bism uth is in the 0; (111) W T I phase. W hile this agrees with the sim plem odel presented above, a realistic description of bism uth requires a theory which incorporates bism uth's ve valence bands[21].

It will be interesting to search form aterials in the ST I phase, which occur on the \other side of diam ond" in our sequence. We hope that the exotic surface properties predicted for this phase will stimulate further experimental and theoreticale orts.

It is a pleasure to thank JoelM oore and Leon B alents for helpfuldiscussions. This work was supported by NSF grants DM R -0079909 and DM R -0605066 and DOE grant DE-FG 02-ER -0145118.

Note added: In subsequent work we have predicted that a number of speci c m aterials are ST I's[22]. These include the sem iconducting alloy B $i_{\rm h}$ x Sb_x as well as - Sn and HgTe under uniaxial strain.

- [1] S.M urakam i, N.N agaosa and S.C. Zhang, Science 301, 1348 (2003).
- [2] J. Sinova et al., Phys. Rev. Lett. 92, 126603 (2004).
- [3] Y K. Kato et al., Science 306, 1910 (2004).
- [4] J. W underlich, B. Kaestner, J. Sinova, T. Jungwirth, Phys. Rev. Lett. 94 047204 (2005).
- [5] C L. K ane and E J. M ele Phys. Rev. Lett. 95 226801 (2005).
- [6] C L. K ane and E J. M ele Phys. Rev. Lett. 95 146802 (2005).
- [7] D. J. Thouless, M. Kohmoto, M. P. Nightingale and M. den Nijs, Phys. Rev. Lett 49, 405 (1982).
- [B] Y.Yao, et al., cond-m at/0606350 (2006); H.M in, et al., cond-m at/0606504 (2006).
- [9] S.Murakami, cond-m at/0607001 (2006).
- [10] JE.M oore and L.Balents, cond-m at/0607314 (2006).
- [11] R.Roy, cond-m at/0607531 (2006).
- [12] L.Fu and C.L.Kane, Phys. Rev. B 74, 195312 (2006).
- [13] R.B. Laughlin, Phys. Rev. B 23, R5632 (1981).
- [14] M.Kohmoto, B.I.Halperin and Y.-S.Wu, Phys. Rev. B 45, 13488 (1992).
- [15] R. Jackiw, Phys. Rev. D 29, 2375 (1984).
- [16] G W .Sem eno , Phys. Rev. Lett. 53, 2449 (1984).
- [17] E.Fradkin, E.D agotto, D.Boyanovsky, Phys. Rev. Lett. 57, 2967 (1986).
- [18] F D M . Haldane, Phys. Rev. Lett. 61, 2015 (1988).
- [19] H. Suzuura and T. Ando, Phys. Rev. Lett. 89 266603 (2002).
- [20] S. Hikami, A. I. Larkin and Y. Nagaoka, Prog. Theor. Phys. 63, 707 (1980).
- [21] Y.Liu and R.E.Allen, Phys. Rev. B 52, 1566 (1995).
- [22] L.Fu and C.L.Kane, cond-m at/0611341 (2006).